AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions and listings of claims in the application:

Listing of Claims

1. (Canceled)

2. (Previously presented) The method as set forth in claim 8, wherein the nitride semiconductor crystal film has the same composition as that of the first conductive nitride semiconductor layer formed thereon.

3. (Previously presented) The method as set forth in claim 8, wherein the nitride semiconductor crystal film is a gallium nitride (GaN) film.

4. (Previously presented) The method as set forth in claim 8, wherein the nitride semiconductor crystal film has a thickness of 1 to 10 micrometers.

5. (Previously presented) The method as set forth in claim 8, wherein the step b) is performed by an HVPE (Hydride Vapor Phase Epitaxy) method.

6. (Previously presented) The method as set forth in claim 5, further comprising a nitridation process of the substrate, before performing the step b).

7. (Previously presented) The method as set forth in claim 8, wherein the step c) is performed at a temperature not exceeding 800°C by making use of hydrogen gas or mixed gases containing hydrogen.

8. (Currently amended) A method of manufacturing a nitride semiconductor light emitting device, said method comprising the steps of:

a) preparing a substrate for use in growth of nitride semiconductors;

b) growing a un-doped nitride semiconductor crystal film on the substrate, the un-doped nitride semiconductor crystal film having a composition represented as $Al_xIn_yGa_{(1-x-y)}N$ ($0 \leq x \leq 1$, $0 \leq y \leq 1$, $0 \leq x+y \leq 1$);

c) performing a surface treatment process on the un-doped nitride semiconductor crystal film by making use of hydrogen gas or mixed gases containing hydrogen, in order to remove an oxide film formed on the un-doped nitride semiconductor crystal film; and

d) successively forming a first conductive nitride semiconductor layer, an active layer, and a second conductive nitride semiconductor layer on the un-doped nitride semiconductor crystal film;

said method further comprising [[the]] a step c') of performing a heat treatment process on the un-doped nitride semiconductor crystal film, in order to improve the surface condition of the nitride semiconductor crystal film in a state wherein the oxide film is removed therefrom, after completing the step c) and before forming the first conductive nitride semiconductor layer,

wherein the step c') is performed at a temperature of 100°C to 1500°C under the environment of gases including at least one selected from the group consisting of ~~Nitrogen, Hydrogen, and Ammonia~~ nitrogen and ammonia.

9. (Previously presented) The method as set forth in claim 8, wherein the step d) is performed by an MOCVD (Metal Organic Chemical Vapor Deposition) method.

10. (Previously presented) The method as set forth in claim 8, wherein the substrate for use in growth of nitride semiconductors is a sapphire substrate or SiC substrate.

11 -21. (Cancelled